

# GAE

# GREAT AMERICAN ELECTRONICS

## DM40-28

Silicon NPN high power UHF transistor DM40-28 is designed for common base wide band amplifier, driver, or oscillator applications in land and mobile and on-board radio systems.

Output Power: 40 Watt  
Frequency Range: 400-1000 Mhz  
Voltage: 28 V  
Package Type: 3/8 Helicopter  
Input Matched  
Common Base Configuration  
Emitter Ballast Resistors  
Aluminum Metalization

### Electrical Characteristics ( $T_{CASE} = 40^{\circ}C$ )

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$P_{out}$	$f_o = 1000 \text{ Mhz} / V_{cc} = 28V / P_{IN} = 13.3W$	20			W
$G_p$	$f_o = 1000 \text{ Mhz} / V_{cc} = 28V / P_{out} = 40W$	5	9	10	dB
$\lambda_c$	$f_o = 1000 \text{ Mhz} / V_{cc} = 28V / P_{out} = 40W$	40	48		%

### ABSOLUTE MAXIMUM RATINGS ( $T_{CASE} = 25^{\circ}C$ )

SYMBOL	PARAMETERS	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	4	V
$I_c$	Continuous Collector Current	4	A
$P_C$	Collector Power Dissipation	66*	W
$T_j$	Junction Temperature	160	$^{\circ}C$
$R_{th(j-c)}$	Junction-Case Thermal Resistance	1.8	$^{\circ}C/W$

\*For Dynamic Operation  $T_{CASE} = 40^{\circ}C$

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